2SC3935G

Silicon NPN epitaxial planar type

For high-frequency amplification/oscillation/mixing

Features

- High transition frequency f_T
- Small collector output capacitance (Common base, input open circuited) C_{ob} and reverse transfer capacitance (Common base) C_{rb}
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	15	V	
Collector-emitter voltage (Base open)	V _{CEO}	10	v	
Emitter-base voltage (Collector open)	V _{EBO}	3	V	
Collector current	I _C	50	mA	
Collector power dissipation	P _C	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

- Package
 - Code
 - SMini3-F2
 - Marking Symbol: 1S
 - Pin Name
 - 1. Base
 - 2. Emitter
 - 3. Collector

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	10		<u>ن</u>	V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = 10 \mu {\rm A}, I_{\rm C} = 0$	3	201		V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 10 V, I_E = 0$	0.	2	1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_B = 0$	0		10	μΑ
Forward current transfer ratio	h _{FE1} *1	$V_{CE} = 2.4 \text{ V}, I_C = 7.2 \text{ mA}$	75		220	
	h _{FE2}	$V_{CE} = 2.4 \text{ V}, I_C = 100 \mu\text{A}$	75			
h _{FE} ratio	Δh_{FE}^{*2}	h_{FE2} : $V_{CE} = 2.4 \text{ V}, I_{C} = 100 \mu\text{A}$	0.75		1.60	_
		h_{FE1} : $V_{CE} = 2.4 \text{ V}, I_C = 7.2 \text{ mA}$	1			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 20 \text{ mA}, I_{\rm B} = 4 \text{ mA}$			0.5	V
Transition frequency	f _T	$V_{CB} = 2.4 \text{ V}, I_E = -7.2 \text{ mA}, f = 200 \text{ MHz}$	1.4	1.9	2.5	GHz
Collector output capacitance	C _{ob}	$V_{CB} = 4 V, I_E = 0, f = 1 MHz$		0.9	1.1	pF
(Common base, input open circuited)						
Reverse transfer capacitance (Common base)	C _{rb}	$V_{CB} = 4 V, I_E = 0, f = 1 MHz$		0.25	0.35	pF
Collector-base parameter	r _{bb} ' • C _C	$V_{CB} = 4 \text{ V}, I_E = -5 \text{ mA}, f = 31.9 \text{ MHz}$		11.8	13.5	ps

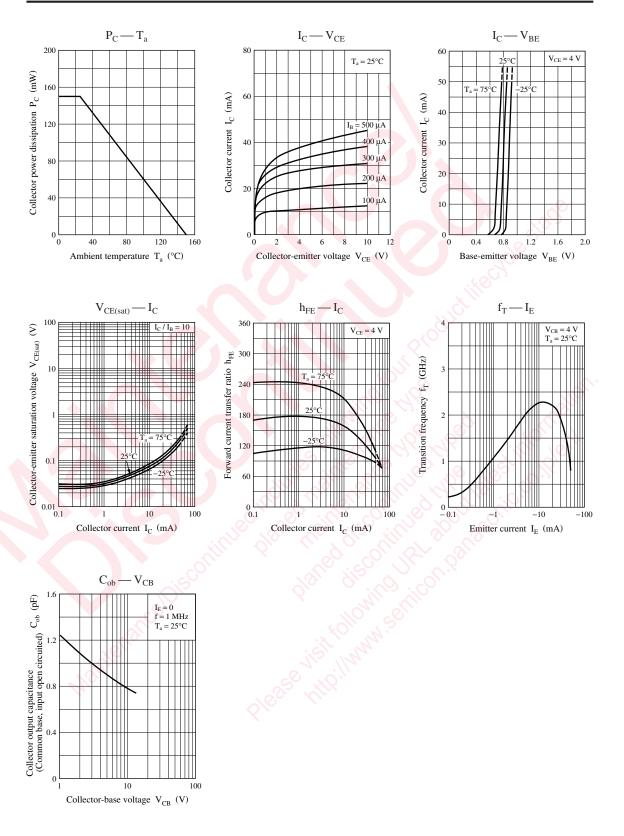
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

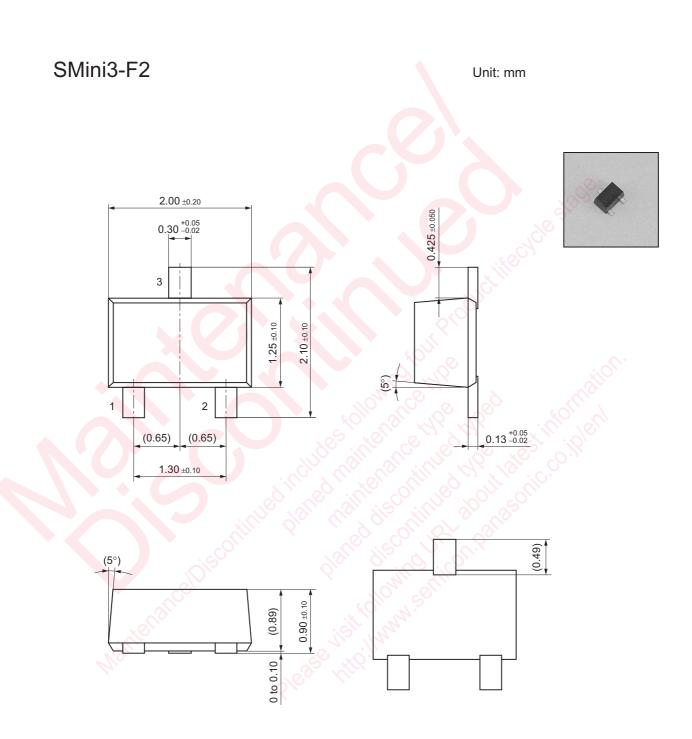
2. *1: Rank classification

Rank	Р	Q
h _{FE}	75 to 130	110 to 220

*2: $\Delta h_{FE} = h_{FE2} / h_{FE1}$

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